

Amendments to the Specification:

Please replace the paragraph starting on page 3, at line 3 with the following amended paragraph:

-- In an embodiment, the material of the contact pressure sensitive layer may be a semi-conductor element from columns III|[B]| Δ and V|[B]| Δ of the Mendeleev table. --

Please replace the paragraph starting on page 3, at line 6 with the following amended paragraph:

-- In another embodiment, the material of the contact pressure sensitive layer is a ternary semi-conductor element from columns III|[B]| Δ and V|[B]| Δ of the Mendeleev table. --

Please replace the paragraph starting on page 5, line 23 with the following amended paragraph:

-- The contact pressure sensor is based on the knowledge of solid state physics, particularly the pressure sensitivity of structures made from semi-conductor elements, especially from columns III|[B]| Δ and V|[B]| Δ of the Mendeleev table. Different column elements are combined, and are grown epitaxially (lattice-matched) on a single substrate. Once contact pressure is applied to the material a difference in resistance can be measured.--

Please replace the paragraph starting on page 7, line 1 with the following amended paragraph:

-- A third layer 26 that acts as a pressure sensitive layer in the contact pressure sensor 10 is deposited on the support layer 24. The pressure sensitive layer 26 is a semi-conductor element such as elements from columns III|[B]| Δ and V|[B]| Δ of the

Mendeleev table, for example, n-type Aluminium Gallium Arsenide (Al_xGal-xAs, or n-type Al_xGa_{1-x}As) with a thickness of but not exclusively 10,000Å, and consists of but not exclusively about 30% Al. --